

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









PNP Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage BC856, SBC856 BC857, SBC857 BC858	V _{CEO}	-65 -45 -30	٧
Collector – Base Voltage BC856, SBC856 BC857, SBC857 BC858	V _{CBO}	-80 -50 -30	V
Emitter - Base Voltage	V _{EBO}	-5.0	V
Collector Current –Continuous	I _C	-100	mAdc
Collector Current – Peak	I _C	-200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR–5 Board (Note 1) T _A = 25°C Derate Above 25°C	P _D	380 250 3.0	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	328	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in

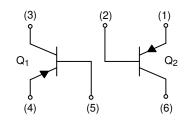


ON Semiconductor®

www.onsemi.com



SOT-363/SC-88 CASE 419B STYLE 1



MARKING DIAGRAM



3x = Specific Device Code x = B, F, G, or L

(See Ordering Information)

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = -10 mA) BC856, SBC856 Series BC857, SBC857 Series BC858 Series	V _{(BR)CEO}	-65 -45 -30	- - -	- - -	V
Collector – Emitter Breakdown Voltage $ \begin{pmatrix} I_C = -10 \ \mu\text{A}, \ V_{EB} = 0 \end{pmatrix} $ BC856, SBC856 Series BC857B, SBC857B Only BC858 Series	V _{(BR)CES}	-80 -50 -30	- - -	- - -	V
Collector – Base Breakdown Voltage (I _C = -10 μA) BC856, SBC856 Series BC857, SBC857 Series BC858 Series	V _{(BR)CBO}	-80 -50 -30	- - -	- - -	V
Emitter – Base Breakdown Voltage (I _E = -1.0 µA) BC856, SBC856 Series BC857, SBC857 Series BC858 Series	V _{(BR)EBO}	-5.0 -5.0 -5.0	- - -	- - -	V
Collector Cutoff Current $(V_{CB} = -30 \text{ V})$ $(V_{CB} = -30 \text{ V}, T_A = 150^{\circ}\text{C})$	I _{CBO}	- -	- -	-15 -4.0	nA μA
ON CHARACTERISTICS					
DC Current Gain	h _{FE}	- - 220 420	150 270 290 520	- - 475 800	-
Collector – Emitter Saturation Voltage $(I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA})$ $(I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA})$	V _{CE(sat)}	- -	- -	-0.3 -0.65	V
Base – Emitter Saturation Voltage $(I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA})$ $(I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA})$	V _{BE(sat)}	- -	-0.7 -0.9	- -	V
Base – Emitter On Voltage ($I_C = -2.0$ mA, $V_{CE} = -5.0$ V) ($I_C = -10$ mA, $V_{CE} = -5.0$ V)	V _{BE(on)}	-0.6 -	- -	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product $(I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ MHz})$	f _T	100	-	-	MHz
Output Capacitance $(V_{CB} = -10 \text{ V}, f = 1.0 \text{ MHz})$	C _{ob}	-	-	4.5	pF
Noise Figure ($I_C = -0.2$ mA, $V_{CE} = -5.0$ Vdc, $R_S = 2.0$ k Ω , $f = 1.0$ kHz, BW = 200 Hz)	NF	-	_	10	dB

TYPICAL CHARACTERISTICS - BC856/SBC856

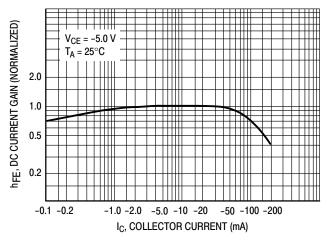


Figure 1. DC Current Gain

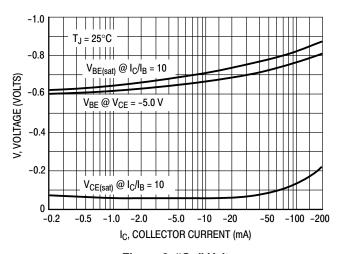


Figure 2. "On" Voltage

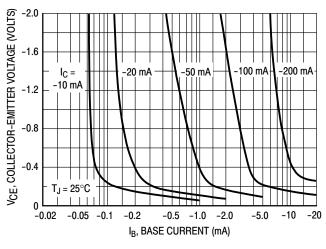


Figure 3. Collector Saturation Region

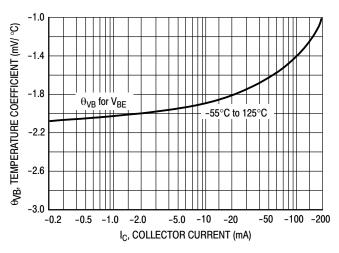


Figure 4. Base-Emitter Temperature Coefficient

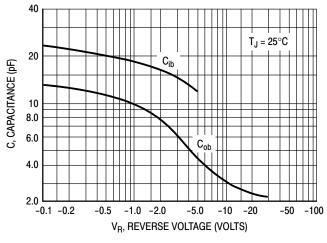


Figure 5. Capacitance

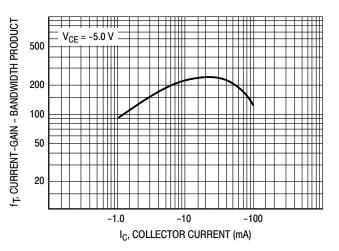


Figure 6. Current-Gain - Bandwidth Product

TYPICAL CHARACTERISTICS - BC857/SBC857/BC858

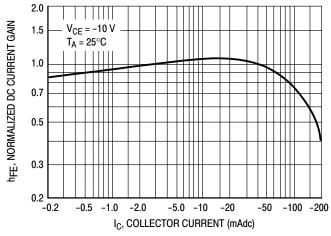


Figure 7. Normalized DC Current Gain

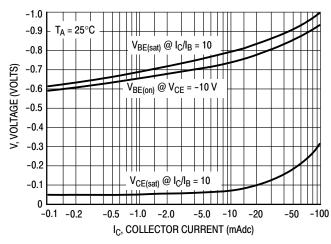


Figure 8. "Saturation" and "On" Voltages

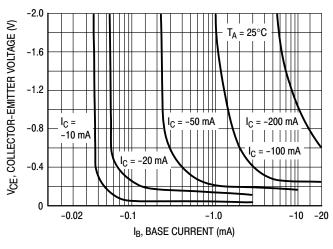


Figure 9. Collector Saturation Region

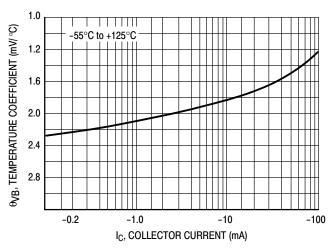


Figure 10. Base–Emitter Temperature Coefficient

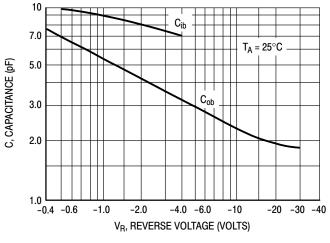


Figure 11. Capacitances

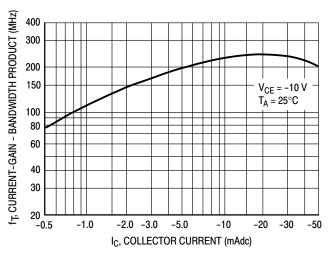


Figure 12. Current-Gain - Bandwidth Product

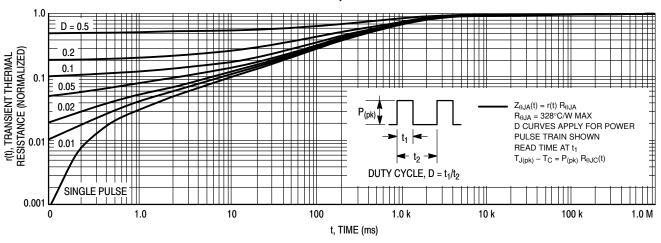


Figure 13. Thermal Response

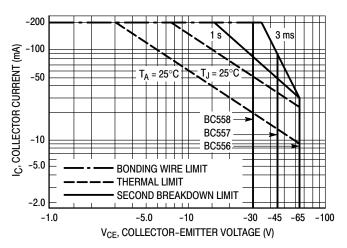


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

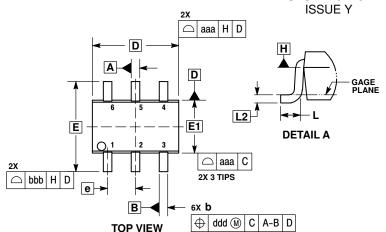
The data of Figure 14 is based upon $T_{J(pk)} = 150^{\circ}C$; T_{C} or T_{A} is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

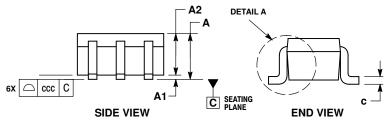
ORDERING INFORMATION

Device	Device Marking	Package	Shipping [†]
BC856BDW1T1G	3B	SOT-363 (Pb-Free)	3,000 / Tape & Reel
SBC856BDW1T1G	3В	SOT-363 (Pb-Free)	3,000 / Tape & Reel
BC856BDW1T3G	3B	SOT-363 (Pb-Free)	10,000 / Tape & Reel
SBC856BDW1T3G	3В	SOT-363 (Pb-Free)	10,000 / Tape & Reel
BC857BDW1T1G	3F	SOT-363 (Pb-Free)	3,000 / Tape & Reel
SBC857BDW1T1G	3F	SOT-363 (Pb-Free)	3,000 / Tape & Reel
BC857CDW1T1G	3G	SOT-363 (Pb-Free)	3,000 / Tape & Reel
SBC857CDW1T1G	3G	SOT-363 (Pb-Free)	3,000 / Tape & Reel
BC858CDW1T1G	3L	SOT-363 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SC-88/SC70-6/SOT-363 CASE 419B-02





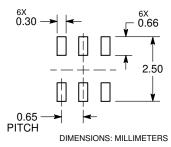
NOTES

- ITES:
 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF
 THE PLASTIC BODY AND DATUM H.
 DATUMS A AND B ARE DETERMINED AT DATUM H.
 DIMENSIONS D AND C APPLY TO THE FLAT SECTION OF THE
 LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION.
 ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN

- ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION & AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α			1.10			0.043	
A1	0.00		0.10	0.000		0.004	
A2	0.70	0.90	1.00	0.027	0.035	0.039	
b	0.15	0.20	0.25	0.006	0.008	0.010	
С	0.08	0.15	0.22	0.003	0.006	0.009	
D	1.80	2.00	2.20	0.070	0.078	0.086	
E	2.00	2.10	2.20	0.078	0.082	0.086	
E1	1.15	1.25	1.35	0.045	0.049	0.053	
е		0.65 BS	С	0	.026 BS	SC	
L	0.26	0.36	0.46	0.010	0.014	0.018	
L2		0.15 BSC 0.006 BSC			SC		
aaa	0.15			0.006			
bbb	0.30			0.012			
ccc		0.10 0.004					
ddd	0.10			0.004			

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:

- PIN 1. EMITTER 2 2. BASE 2
 - 3. COLLECTOR 1 4. EMITTER 1

 - 5. BASE 1 6. COLLECTOR 2

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative